

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (CANCELLED)

13. (NEW) A semiconductor light emitting element comprising as a lamination structure:

an insulating substrate;

GaN-based stacked films stacked/formed on said insulating substrate, one of these films being a GaN-based film grown by using a selective growth mask material layer containing a fluorescent substance; and

an active layer, formed on the GaN-based stacked films, for emitting at least a visible light component,

wherein said fluorescent substance converts the visible light emitted by said active layer.

14. (NEW) The semiconductor light emitting element according to claim 13, wherein said visible light emitted by said active layer mainly consists of a blue light.

15. (NEW) The semiconductor light emitting element according to claim 13, wherein said fluorescent substance is $(Ba, Ca)B_4O_7$, $(Ca, Sr)_2P_2O_7$ or a mixture of them.

16. (NEW) The semiconductor light emitting element according to claim 13, further comprising a protective film containing the fluorescent substance on a topmost layer.

17. (NEW) The semiconductor light emitting element according to claim 1, wherein said light emitting layer includes an $A_{1-x}In_yGa_{1-x-y}N$ ($0 \leq x \leq 0.1 \leq y \leq 1$) film, or a $B_2Ga_{1-z}N$ ($0 \leq z \leq 1$) film.

18. (NEW) The semiconductor light emitting element according to claim 13, wherein the selective growth mask material layer containing said fluorescent substance is formed in a stripe shape.

19. (NEW) The semiconductor light emitting element according to claim 13, wherein the selective growth mask material layer containing said fluorescent substance is formed in a grid shape.

20. (NEW) The semiconductor light emitting element according to claim 13, wherein the selective growth mask material layer containing said fluorescent substance is formed in a polka-dot pattern.

21. (NEW) The semiconductor light emitting element according to claim 13, further comprising a lens formed on a back surface side of said insulating substrate.

22. (NEW) The semiconductor light emitting element according to claim 13, wherein a thickness of the mask layer containing said fluorescent substance is in a range of 50 nm to 20 μ m.